



IMPACT OF NANOCRYSTALLINE OXIDE IN CRYSTALLINE SEMICONDUCTOR THIN FILMS

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ABSTRACT

In this study, the structural, electrical, and optical characteristics of Na-doped NiO thin films were analysed. The bunch air-filled deposition of 0.1 M Na-doped NiO thin films at a substratum temperature of 420 °C was achieved. After analysing the XRD spectra of Na-doped NiO thin films, it was originate that these films have a monocrystalline structure with a cubic structure, with only a single (111) peak. At a concentration of 3 wt%, Na doped NiO thin films had a maximum crystallite size of 18.90 nm. When comparing undoped and Na-doped NiO thin films, the latter exhibits a higher optical transmission spectrum in the visible range. When Na was doped into the material at a concentration of 2 weight percent, the band gap energy was reduced to a minimum of 3.53 eV. With a 3 wt% mass fraction, the Urbach energy drops to as little as 0.312 eV. Electrical resistance in Na-doped NiO films is on the order of 5%. Na doping is most effective when applied in a 3 percent solution.

Keywords: Na doping, thin films, NiO, TCO, spray pneumatic technique, Urbach energy, semiconductors.

1. INTRODUCTION

Metal oxides can take on a change of organizational geometries, each with their own unique electric construction and set of resulting physical and chemical properties. [1] That's why metal oxides are the backbone of the biochemical and chemical transduction and sensing industries. Their single and flexible physical possessions are put to good use in electrical and optoelectronic devices. Scientific and practical interests have kept the study of nanostructured metal oxides active.

Because of their possible applications in various technologies, such as gas sensors, photochemical, photoconductive devices, solar cells, lithium-ion batteries, liquid crystal displays, gas discharge displays, and more, they have recently received a great deal of attention. Because of its n-type semiconductor nature, SnO₂ is ideal for use in gas sensing devices. The size of the crystal forming the gas response layer is inversely proportional to the total air warmth and the sign constancy it provides. For the optimal air response, the grain size should be

no more than twice as large as the depletion layer. Due to the wide conductivity of semiconductor metal oxide gas sensors like ZnO, WO₃, and SnO₂, which react to oxidising and decomposing gases, this phenomenon has been the subject of extensive research. Materials in large quantities are their specialty. Because of their higher surface-to-volume ratio, thin-film gas sensors are preferable over thick-film sensors. Power plants that use fuel cells are the most efficient, quietest, and cleanest option available today. For this reason, hydrogen will soon be the primary fuel source for power plants.[3]

It is clearly obvious that in all of these uses, safety measures are of the utmost importance because of hydrogen's explosive qualities. A variety of tin oxide (SnO₂) thin films have been prepared using a variety of methods. In addition, these include, activated reactive evaporation, sputtering, chemical vapour deposition ion beam aided deposition, as well as spray-pyrolysis. In addition to being easy, reproducible, and economical, the sol-gel dip coating process is also appropriate for wide area applications. [2] It's only in the last decade or two that the numerous advantages it offers over other methods have sparked significant attention in the scientific and industrial communities. There are many advantages to using sol-gel dip coating, including lower energy usage and a lower environmental impact.

The combination of nanocrystallinity and nanoporosity can yield fascinating physical and chemical features since of their enormous surface-to-volume relations and the likely occurrence of regions with high surface energy and phase compositions differing from those in the bulk. NiO-based nanomaterials have received the most interest for use in gas sensors and other applications, including electrochromic devices and various types of catalysts. In addition to acetone and ammonia, other gases detected by the instrument include ethanol and formaldehyde, as well as hydrogen and hydrogen sulfide, as well as methanol, nitrogen dioxide, toluene, and trimethylamine. Electron transfer occurs at interfaces between neighbouring particles in conductometric gas sensors when they are exposed to gases that cause surface-chemical reactions with consequent electron transfer, and it is evident that the technique for producing this material is critical to its function. [4]

2. MATERIALS

- **In the process of making a spray solution**

Dissolving x wt. percent sodium chloride dehydrate (NaCl₂. 2H₂O) solutions and 0.1M (NiCl₂. 6H₂O) nickel chloride hexahydrate yielded sodium chloride dehydrate (NaCl₂. 2H₂O) and 0.1M (NiCl₂. 6H₂O) nickel chloride hexahydrate solutions. As a stabilising step, the combinations were liquified in an equivalent volume of pure, 99.99% ethanol solution and agitated for 120 minutes at 50°C to produce a clear, transparent liquid. The mixtures were then removed from the solvent and dried under a vacuum.

- **Deposition of thin films**

Using a spray pneumatic method, which produces a stream of fine and homogenous droplets with an average diameter of 25 m, the NiO:Na solutions were applied to the intense crystal substrates. As the substrate was heated

to 420 degrees Celsius, a deposition rate of 2 mL/min was achieved. It has been found that NiO: Na films can have doping levels anywhere from 0% by weight to 5% by weight for different concentrations of Na.

- **Characterization**

The XRD (X-ray diffraction) technique was castoff to examine the structural features of Na-doped NiO films at changed angles 20° to 50° using CuK radiation ($= 0.15406\text{nm}$) (XRD Bruker AXS-8D). Optic transmission and electrical resistance were evaluated using an (LAMBDA 25) four-point methods and ultraviolet-visible spectrophotometer, respectively.

3. RESULT AND DISCUSSIONS

Na doped NiO thin film X-ray spreading ranges for a range of Na doping concentrations. To define the crystalline structure, the Bragg peak locations were used; the interplanar distance is a intermittent role of Miller indices (h k l). In contrast, the strengthening of the crystalline structure of NiO thin films doped Na can account for the smaller crystallite size seen with decreasing a_0 – a fluctuation. Na doping has an effect on optical characteristics, which may be seen, for instance, in the optical spread spectrum of NiO thin films doped Na as a function of nitrate concentration. Thin NiO films benefit from Na doping in terms of increased optical transmission. NiO thin films doped Na have a 35–60% transmission in the visible spectrum. A larger average crystallite size is responsible for the improved visible light transmission observed in NiO thin films doped Na.

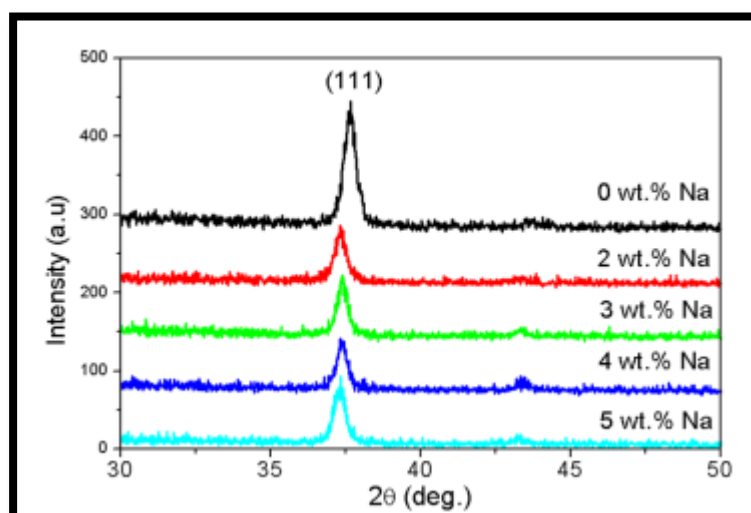


Fig 1. NiO thin films doped Na with a range of doping values

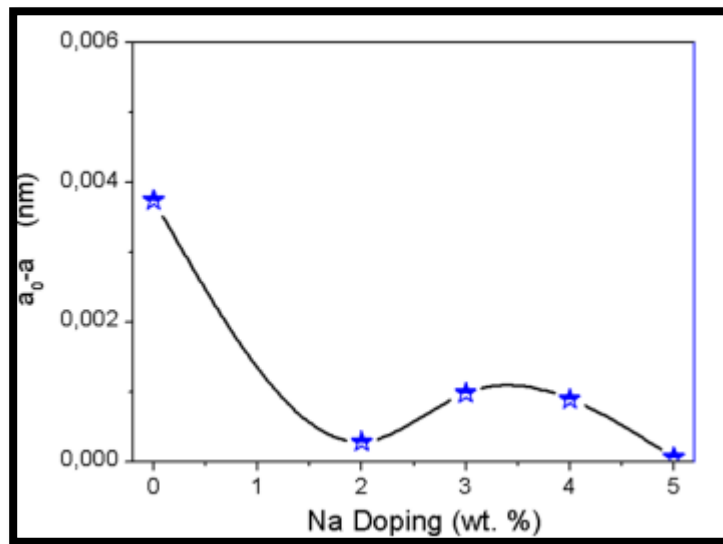


Fig 2. A shift in the position of the (111) peak for NiO thin films doped Na

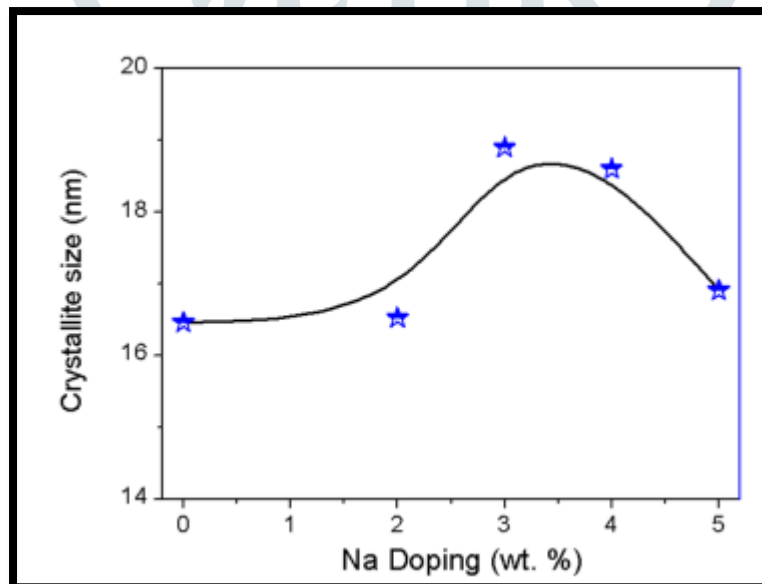


Fig 3. illustrates how the size of the crystallites in NiO thin films doped Na varies as a purpose of doping concentration.

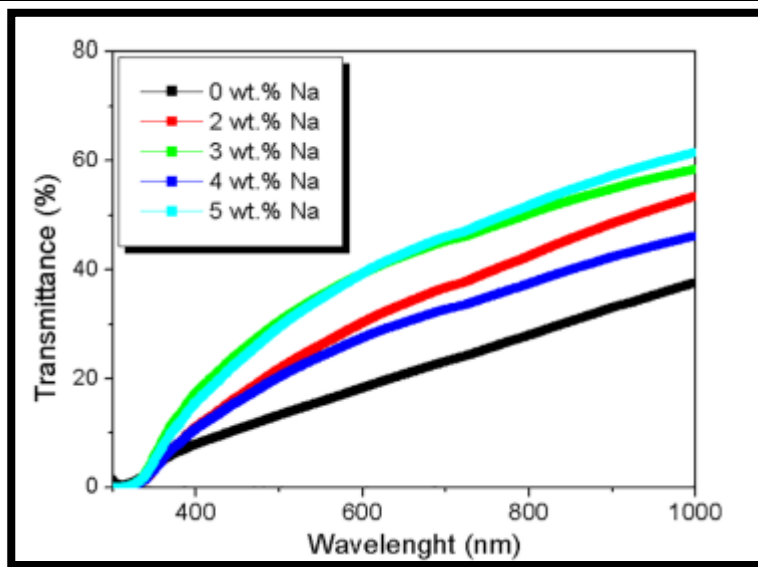


Fig 4. Broadcast spectra of NiO thin films doped Na vs. Na-content

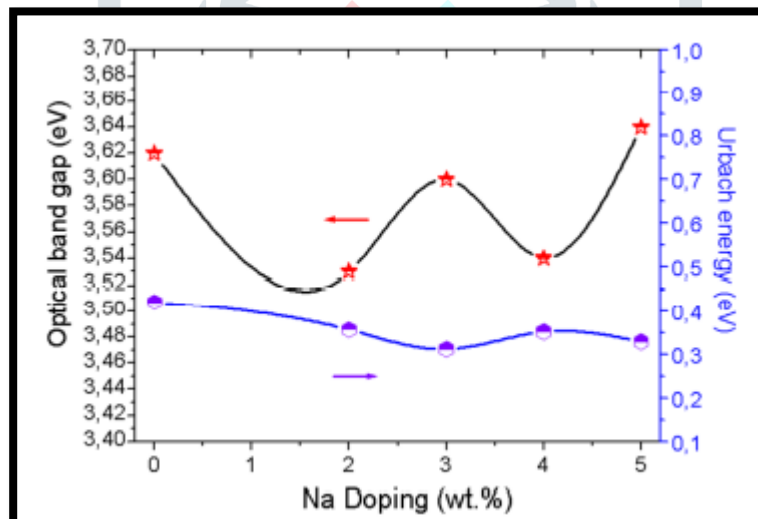


Fig 5. shows how the Urbach energy and optical band gap of NiO thin films doped Na change with increasing doping.

4. CONCLUSIONS

A single (111) peak will see in the NiO thin films doped Na. The greatest crystallite size of NiO thin films doped Na was 18.90 nm at a concentration of 3% by weight. There was a consistent increase in the visible-band visual show ranges of NiO thin films doped Na compared to the undoped. At a concentration of 2 percent, the band gap

energy decreases to a record low of 3.53 eV. At 3% by weight, the calculated energy was determined to be as low as 0.312 eV. Electrical resistance in NiO films is as low as 5 watts at its lowest. Spray-deposited Na-doped NiO thin films provide the most accurate optical, electrical, and structural characterizations.

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